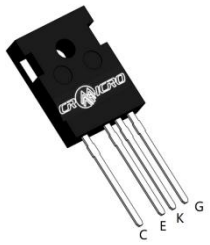
General Description：

Using owner proprietary trench design and advanced Field Stop (FS) technology, offering superior conduction and Switching performances. RoHS Compliant.

V_{CES}	650	V
I_C	75	A
P_{tot} (T_C=25℃)	468	W
$V_{CE(sat)}$	1.40	V

Outline ： TO-247-4



Features：

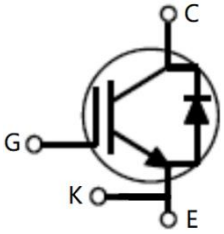
- Ultra-low switching losses due to the combination of Trench FS IGBT and SiC SBD technology;
- FS Trench Technology, Positive temperature coefficient;
- Low saturation voltage：

  $V_{CE(sat)}$,TYP=1.40V @I_C=75A,V_{GE}=15V.

Applications

- Solar inverter

Inner Circuit:



Package Parameters

Type	Marking	Package	Packing	Qty
CRG75T65AQF5SCDZ	G75T65AQF5SCDZ	TO-247-4	Tube	25

Absolute Maximum Ratings（T_C= 25℃ unless otherwise specified）：

Symbol	Parameter	Rating	Unit
V_{CES}	Collector-Emitter Voltage	650	V
V_{GES}	Gate- Emitter Voltage	±20	V
V_{GES}	Gate- Emitter Voltage（tp≤10us,D<0.01）	±30	V
I_C[a1]	Collector Current @T_C = 25 °C	90	A
	Collector Current @T_C = 100 °C	75	
I_{CM}[a1]	Pulsed Collector Current	300	A
I_F[a2]	Diode Continuous Forward Current @T_C =25 °C	80	A
	Diode Continuous Forward Current @T_C = 100 °C	64	
I_{FM}	Diode Maximum Forward Current	180	A
P_D	Power Dissipation @ T_C = 25°C	468	W
	Power Dissipation @ T_C = 100°C	234	W
T_j[a3]	Operating Junction temperature range	-40～175	℃
T_{stg}	Storage Temperature Range	-55～150	℃
T_L	Maximum Temperature for Soldering	270	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R\theta_{JC}$	Thermal Resistance, Junction to case for IGBT	--	0.32	℃/W
$R\theta_{JC}$	Thermal Resistance, Junction to case for Diode	--	1.03	℃/W
$R\theta_{JA}$	Thermal Resistance, Junction to Ambient	--	40	℃/W

Electrical Characteristics of the IGBT（T_C= 25℃ unless otherwise specified）：

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
OFF Characteristics						
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	V_{GE}=0V,I_{CE}=250uA	650	--	--	V
I_{CES}	Collector Cut-off Current	V_{GE}=0V,V_{CE}=650V	--	--	1	mA
$I_{GES(F)}$	Gate-Emitter Forward Leakage Current	V_{GE}=+20V	--	--	+250	nA
$I_{GES(R)}$	Gate-Emitter Reverse Leakage Current	V_{GE} =-20V	--	--	-250	nA
ON Characteristics						
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=75A,V_{GE}=15V @ T_C = 25°C	--	1.40	1.9	V
		I_C=75A,V_{GE}=15V @ T_C =175°C	--	1.62	--	V
$V_{GE(th)}$	Gate - Emitter Threshold Voltage	I_C=0.25mA,V_{CE}=V_{GE}	3.5	--	6.5	V
Pulse width tp≤300μs,δ≤2%						

Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE}=30V,V_{GE}=0V f=1MHz	--	5371	--	pF
C_{oes}	Output Capacitance		--	524	--	
C_{res}	Reverse Transfer Capacitance		--	21	--	
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{CE}=400V,I_C=75A, R_g=10Ω,V_{GE}=15V, Inductive Load, T_J=25℃,	--	30	--	nS
t_r	Rise Time		--	25	--	
$t_{d(off)}$	Turn-Off Delay Time		--	241	--	
t_f	Fall Time		--	20.5	--	
E_{on} [a4]	Turn-On Switching Loss		--	0.62	--	mJ
E_{off}	Turn-Off Switching Loss		--	1.09	--	
E_{ts}	Total Switching Loss		--	1.71	--	
$t_{d(on)}$	Turn-on Delay Time	V_{CE}=400V,I_C=75A, R_g=10Ω,V_{GE}=15V, Inductive Load, T_J=175℃	--	28.5	--	nS
t_r	Rise Time		--	31	--	
$t_{d(off)}$	Turn-Off Delay Time		--	275	--	
t_f	Fall Time		--	42.2	--	
E_{on} [a4]	Turn-On Switching Loss		--	0.82	--	mJ
E_{off}	Turn-Off Switching Loss		--	1.51	--	
E_{ts}	Total Switching Loss		--	2.33	--	
Q_g	Total Gate Charge	V_{CE}=520V,I_C=75A, V_{GE}=15V,	--	184	--	nC
Q_{ge}	Gate to Emitter Charge		--	37	--	
Q_{gc}	Gate to Collector Charge		--	90	--	
Electrical Characteristics of the DIODE						
V_F	Diode Forward Voltage	I_F=75A, TC=25℃	--	1.85	2.5	V
		TC=175℃	--	2.5	--	V
t_{rr}	Reverse Recovery Time	V_R=400V,R_g=10Ω, I_F=75A, di/dt=200A/μS, TC=25℃	--	29	--	nS
Q_{rr}	Reverse Recovery Charge		--	50	--	nC
I_{rrm}	Reverse Recovery Current		--	3.5	--	A

Notes:

a1: The collector DC current is limited by the maximum junction temperature, limited by the bond wire current capacity at 25° C

a2: SiC Diode DC forward current is limited by the maximum junction temperature, limited by the bond wire current capacity at 25° C

a3: Repetitive rating; pulse width limited by maximum junction temperature; Under overloading conditions, it is allowed to operate under the maximum junction temperature T_j=175℃, and the maximum duty cycle is less than 20% (maximum lasting 60s)

a4: Turn-on losses include diode losses

Typical Performance Characteristics

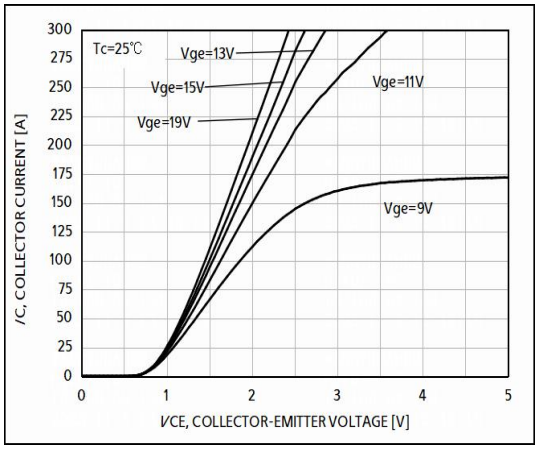


Figure 1. Output Characteristics

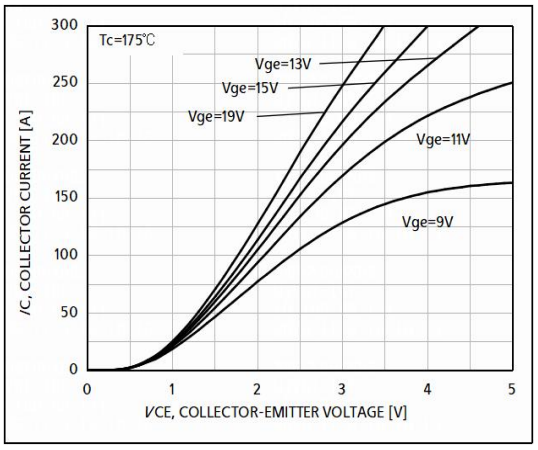


Figure 2. Output Characteristics

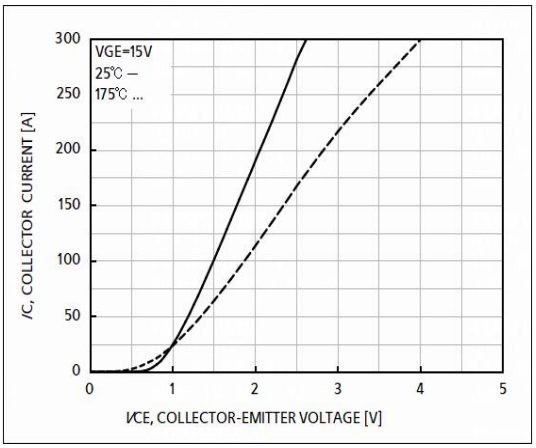


Figure 3. Saturation Voltage Characteristics

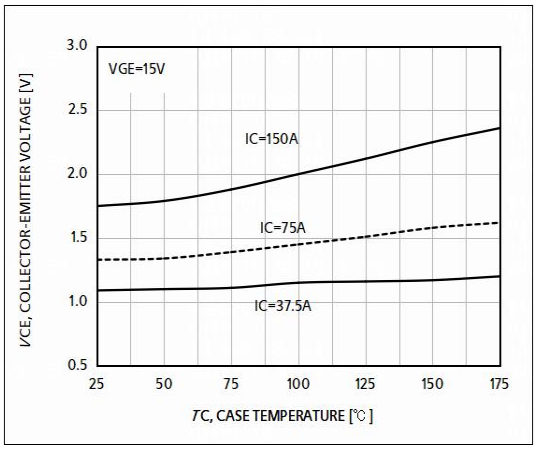


Figure 4. Saturation Voltage -T_C Characteristics

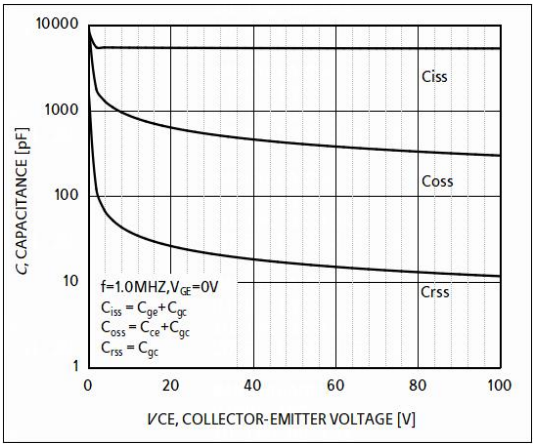


Figure 5. Capacitance Characteristics

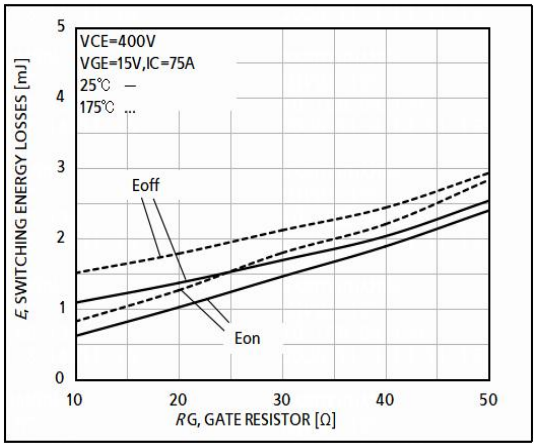


Figure 6. Switching Loss-R_G Characteristics

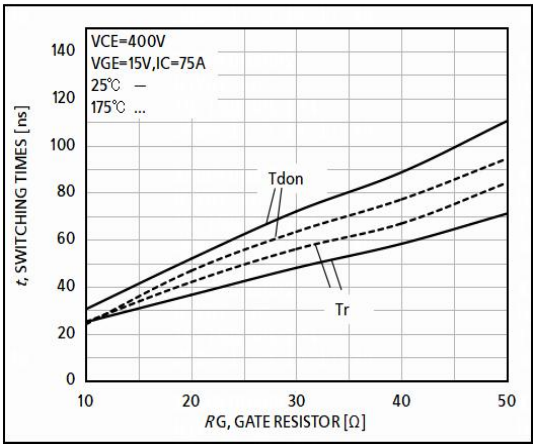


Figure 7. Switching Time-R_G Characteristics

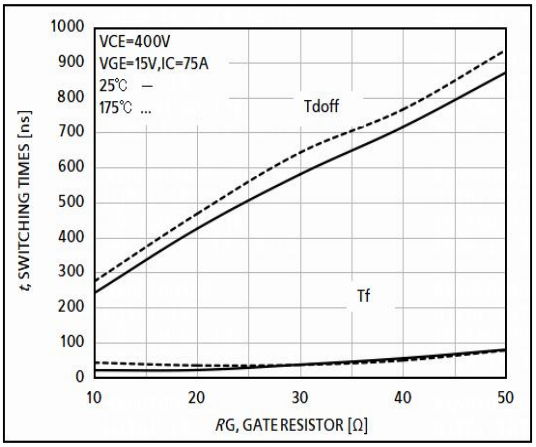


Figure 8. Switching Time-R_G Characteristics

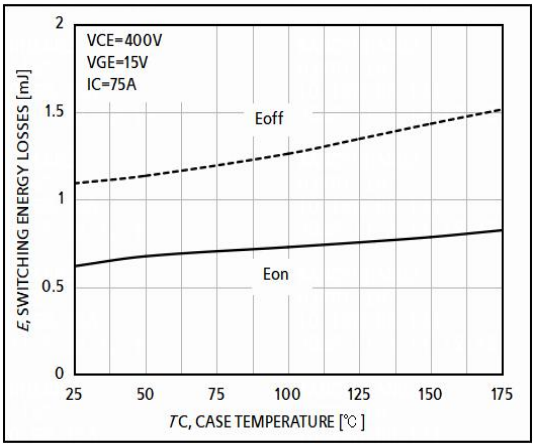


Figure 9. Switching Loss-T_C Characteristics

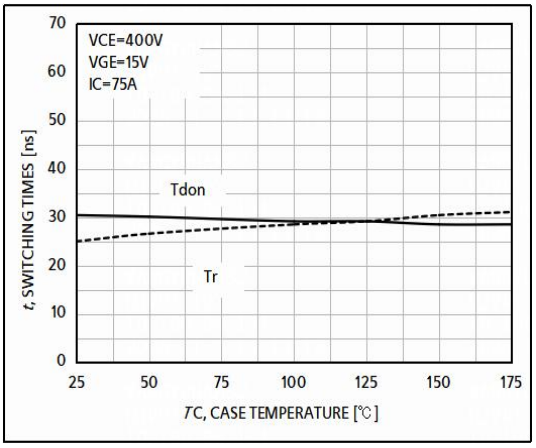


Figure 10. Switching Time-T_C Characteristics

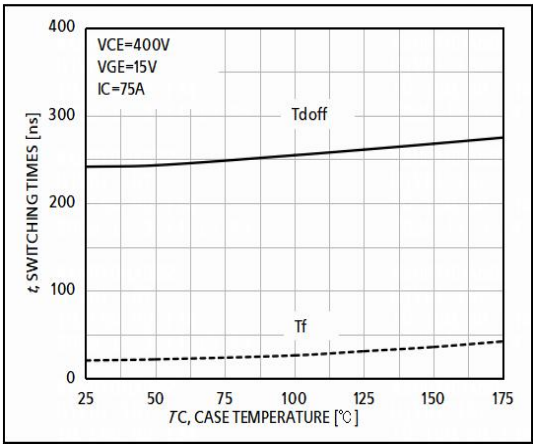


Figure 11. Switching Time-T_C Characteristics

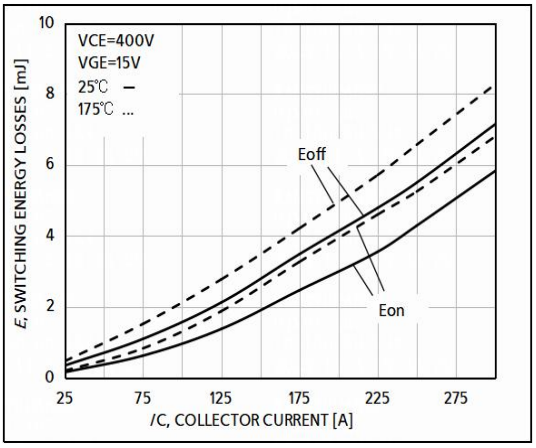


Figure 12. Switching Loss-I_C Characteristics

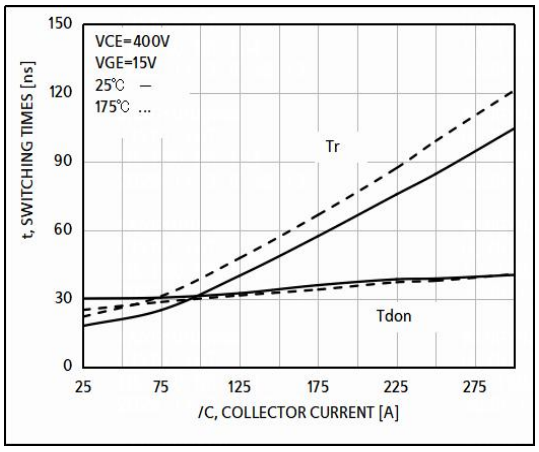


Figure 13. Switching Time-I_C Characteristics

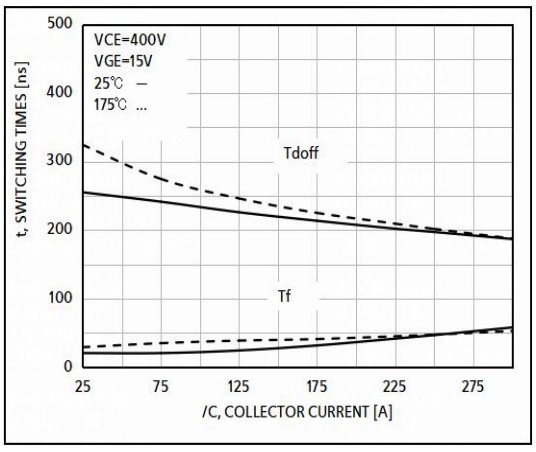


Figure 14. Switching Time-I_C Characteristics

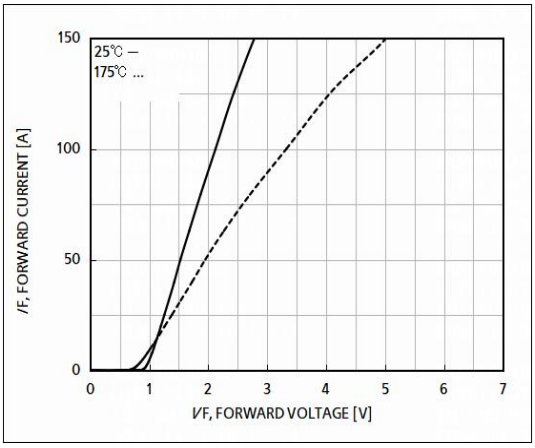


Figure 15. Diode Forward Characteristics

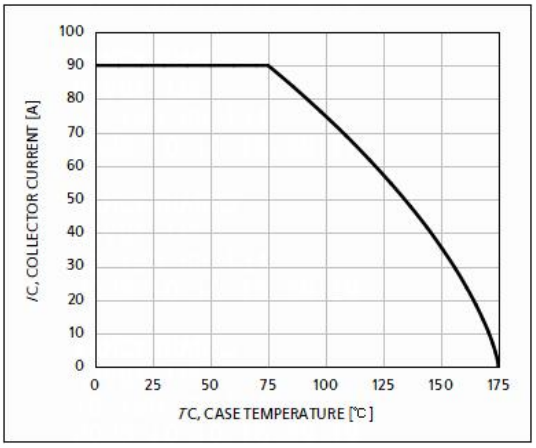


Figure 16. Collector Current-T_C Characteristics
(Tj ≤175℃)

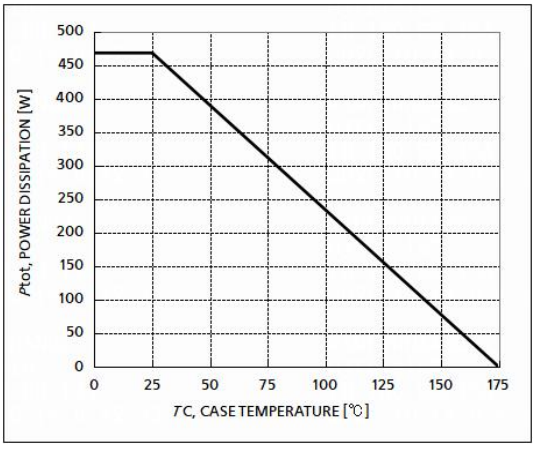


Figure 17. Power Dissipation-T_C Characteristics
(Tj ≤175℃)

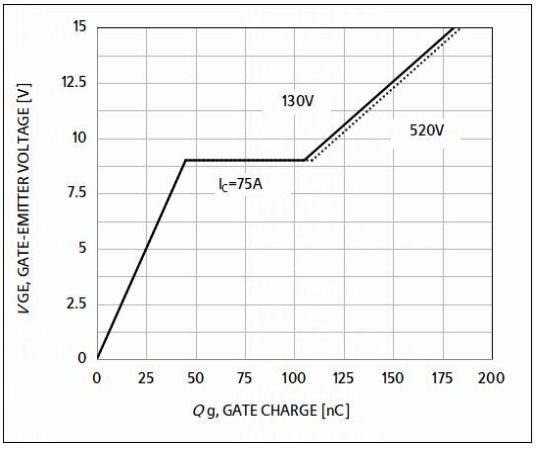


Figure 18. Gate Charge Characteristics

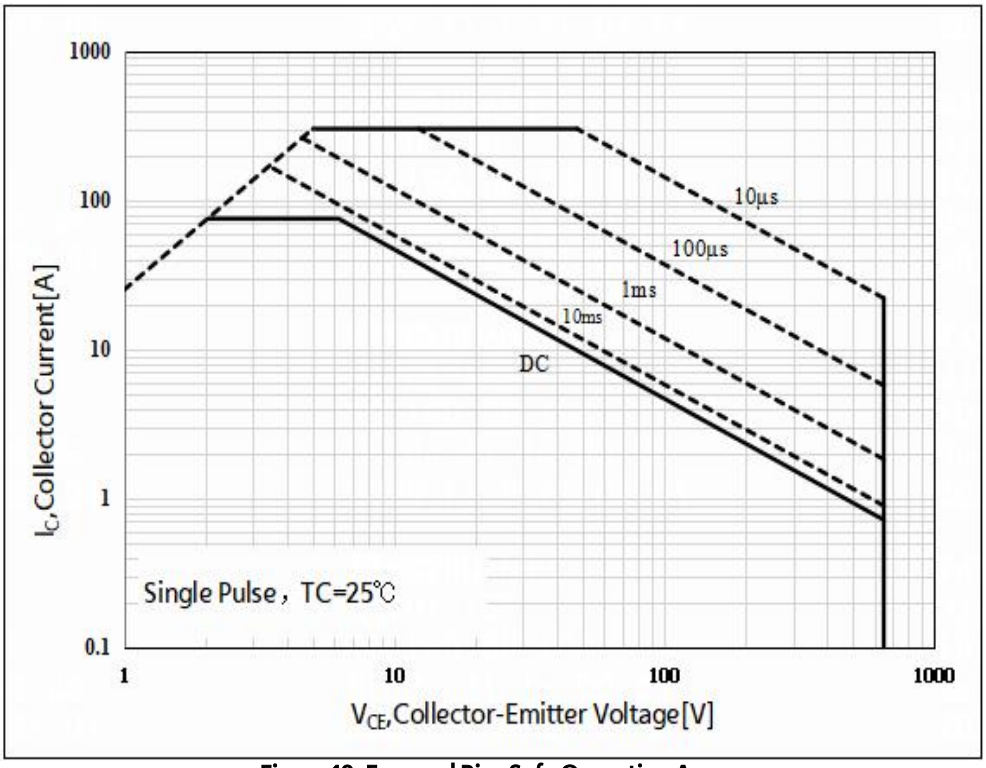


Figure 19. Forward Bias Safe Operating Area

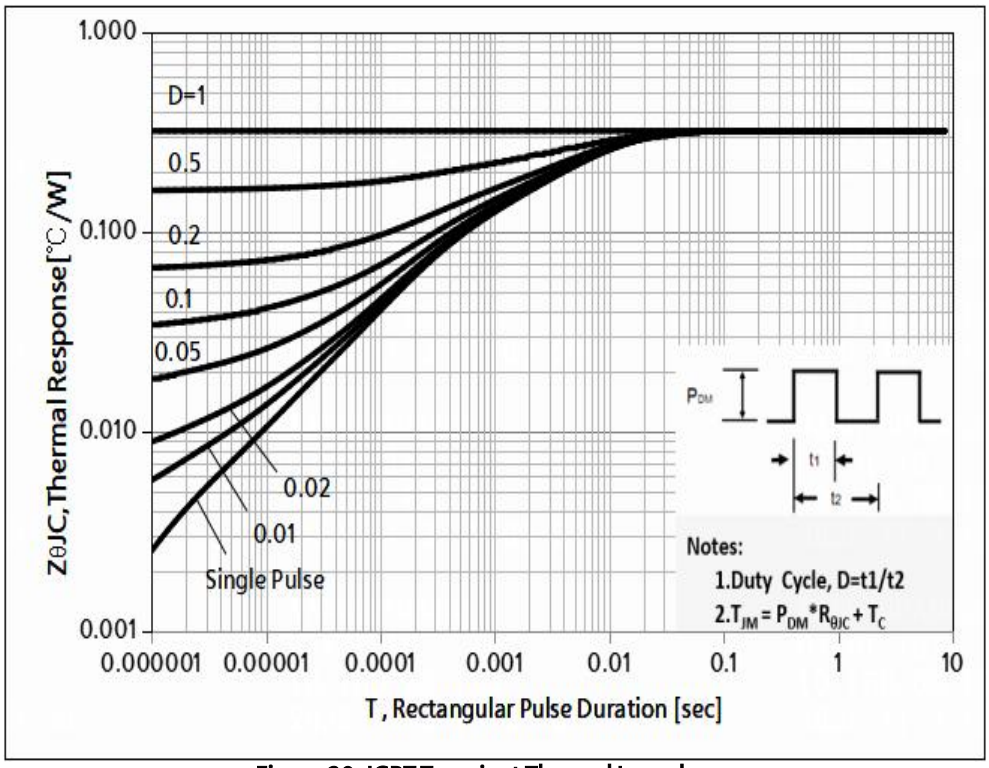
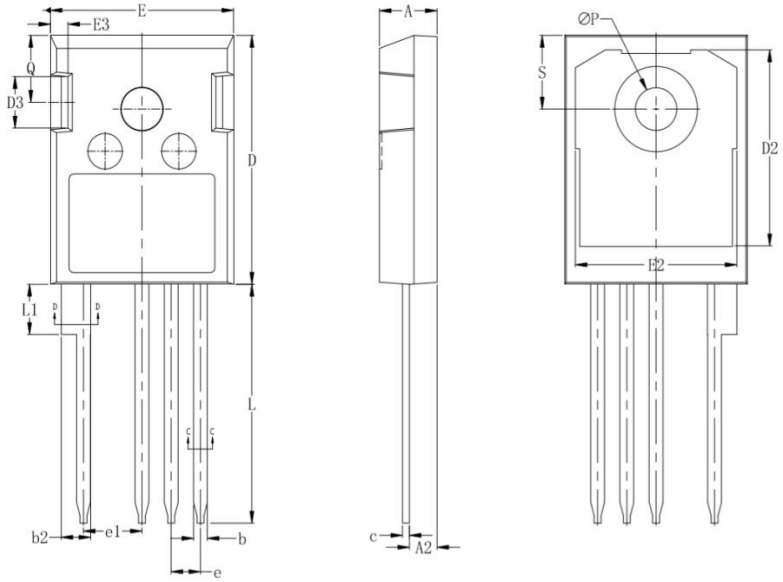


Figure 20. IGBT Transient Thermal Impedance

Package Information



Items	Values(mm)	
	MIN	MAX
A	4.8	5.2
A2	2.2	2.6
b	1.05	1.4
b2	2.4	2.75
c	0.5	0.75
D	20	21.5
D2	15.5	17.2
D3	4	5
E	15.5	16.1
E2	13	15
E3	1	2
e	2.54BSC	
e1	5.08BSC	
L	19	21
L1	4	4.45
ΦP	3.5	3.7
Q	5.4	5.9
S	5.9	6.4

TO-247-4 Package

The name and content of poisonous and harmful material in products

Part's Name	Hazardous Substance									
	Pb	Hg	Cd	Cr(VI)	PBB	PBDE	DIBP	DEHP	DBP	BBP
Limit	⩽ 0.1%	⩽ 0.1%	⩽0.01 %	⩽0.1%	⩽0.1 %	⩽0.1 %	⩽0.1 %	⩽0.1 %	⩽0.1 %	⩽0.1 %
Lead Frame	○	○	○	○	○	○	○	○	○	○
Molding	○	○	○	○	○	○	○	○	○	○
Chip	○	○	○	○	○	○	○	○	○	○
Wire Bonding	○	○	○	○	○	○	○	○	○	○
Plating	○	○	○	○	○	○	○	○	○	○
Solder	×	○	○	○	○	○	○	○	○	○
Note	○: Indicates that the content of this hazardous substance meets the limit requirements of EU RoHS Directive. ×: Indicates that the content of this hazardous substance exceeds the limit requirements of EU RoHS Directive. The solder used in the product contains lead (Pb), but it falls within the exemption scope of the EU RoHS Directive.									

Warnings

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximum ratings of the device.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. IGBTs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. This publication is made by Huajing Microelectronics and subject to regular change without notice.

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Application and Service: Post: 214061 Tel / Fax: 0510-85807228-3399 / 2227

Revison History		
Revision	Date	Major changes
1.0	2025/11/11	Initial release